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June 2014

## **FQA36P15**

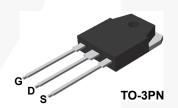
# P-Channel QFET® MOSFET -150 V, -36 A, 90 mΩ

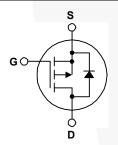
## **Features**

- Low Gate Charge (Typ. 81 nC)
- Low Crss (Typ. 110 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating

## **Description**

• -36 A, -150 V,  $R_{DS(on)}$  = 90 m $\Omega$  (Max) @V<sub>GS</sub> = -10 V,  $I_D$  = -18 A This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQA36P15	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		-150	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		-36	А	
	- Continuous (T <sub>C</sub> = 100°C)		-25.5	Α	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-144	Α	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy		1400	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	-36	A	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	29.4	mJ	
dv/dt	Peak Diode Recovery dv/dt (N		-5.0	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		294	W	
	- Derate above 25°C		1.96	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C	
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C		

### **Thermal Characteristics**

Symbol	Parameter	FQA36P15	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.51	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA36P15	FQA36P15	TO-3PN	Tube	N/A	N/A	30 units

## **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Charac	teristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-150			V
$\Delta BV_{DSS}/$ $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 μA, Referenced to 25°C		-0.13		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -150 V, V <sub>GS</sub> = 0 V			-10	μΑ
		V <sub>DS</sub> = -120 V, T <sub>C</sub> = 150°C			-100	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = -25 V, V <sub>DS</sub> = 0 V	-		-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V			100	nA
On Charact	eristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-2.0		-4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -18 A		0.076	0.09	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = -40 V, I <sub>D</sub> = -18 A	\	19.5		S
Dynamic Cl	haracteristics				1	
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$	\	2550	3320	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz	\	710	920	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			110	140	pF
Switching C	Characteristics				l.	
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -75 \text{ V}, I_{D} = -36 \text{ A},$		50	110	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		350	710	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			155	320	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		150	310	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = -120 V, I <sub>D</sub> = -36 A,		81	105	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -10 V	/	19		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)	- J-	42		nC
Drain-Source	Diode Characteristics and Maximum Ratings	3				
I <sub>S</sub> Maximum Continuous Drain-Source Diode Forward Current					-36	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				-144	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -36 A			-4.0	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -36 A,		198		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		1.45		μС

#### Notes

<sup>1.</sup> Repetitive rating: pulse-width limited by maximum junction temperature.

<sup>2.</sup> L = 1.45 mH, I  $_{AS}$  = -36 A, V  $_{DD}$  = -50 V, R  $_{G}$  = 25  $\Omega,$  starting T  $_{J}$  = 25°C.

<sup>3.</sup> I  $_{SD} \le$  -36 A, di/dt  $\le$  300 A/µs, V  $_{DD} \le$  BV  $_{DSS},$  starting T  $_{J}$  = 25°C.

<sup>4.</sup> Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

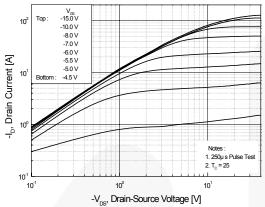
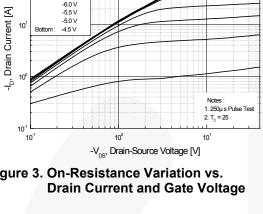


Figure 3. On-Resistance Variation vs.



**Figure 2. Transfer Characteristics** 

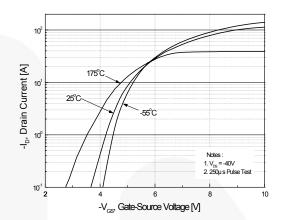


Figure 4. Body Diode Forward Voltage **Variation vs. Source Current** and Temperatue

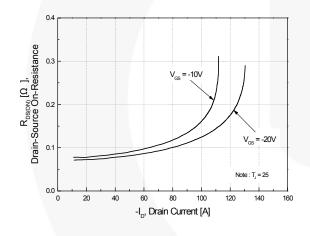
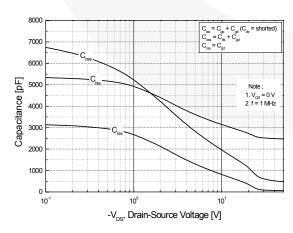
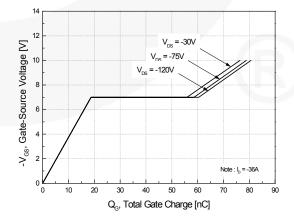


Figure 5. Capacitance Characteristics



Reverse Drain Current [A] Notes: 1. V<sub>cs</sub> = 0V 2. 250µs Pulse Test 10<sup>-1</sup> — 0.0 3.5 0.5 3.0 4.0 -V<sub>SD</sub>, Source-Drain voltage [V]

Figure 6. Gate Charge Characteristics



## Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

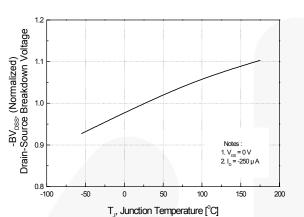


Figure 8. On-Resistance Variation vs. Temperature

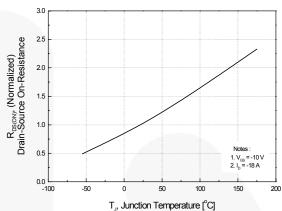


Figure 9. Maximum Safe Operating Area

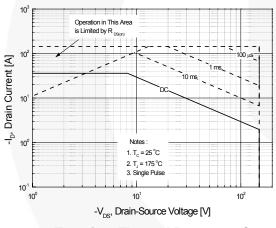


Figure 10. Maximum Drain Current vs. Case Temperature

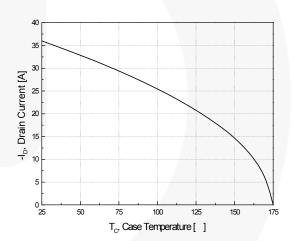
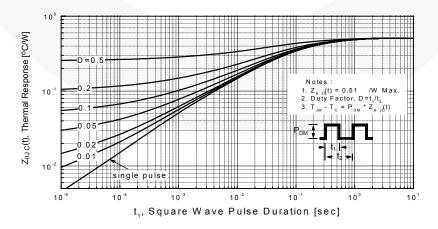


Figure 11. Transient Thermal Response Curve



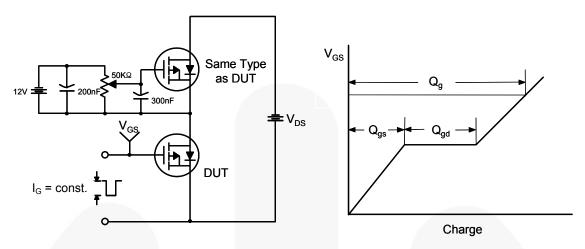


Figure 12. Gate Charge Test Circuit & Waveform

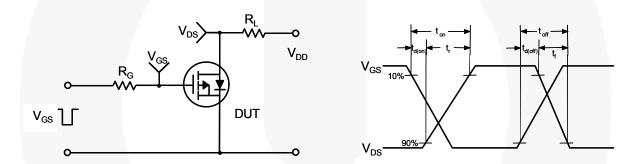


Figure 13. Resistive Switching Test Circuit & Waveforms

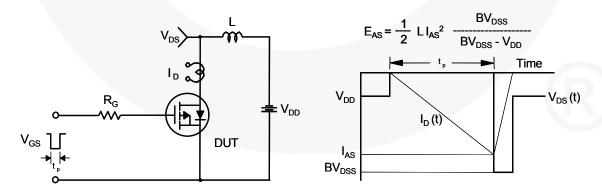


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

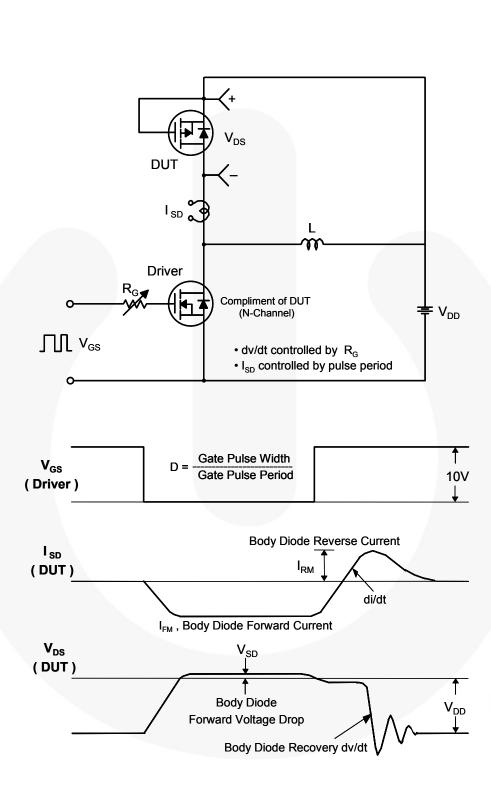
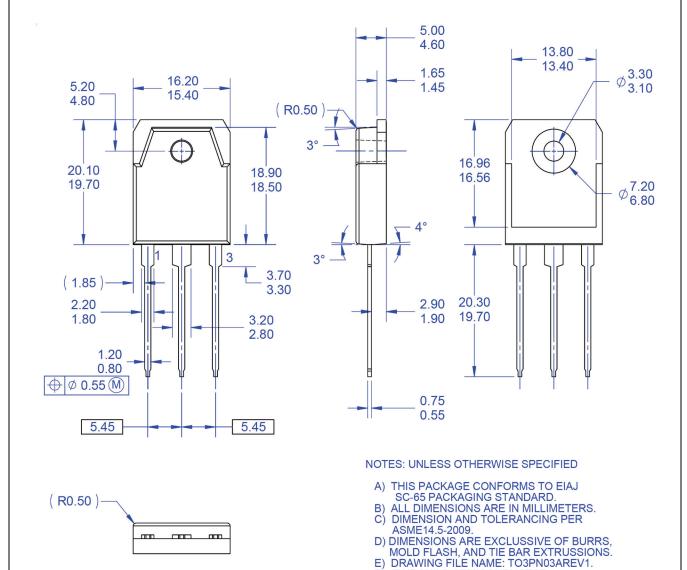


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**



## Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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